

ABSTRACT

Disclosed is a method of the present invention relates to a high voltage transfer circuit. The high voltage transfer circuit includes a first high voltage switch for transferring a high voltage generated within a chip to the outside of the chip according to a clock signal and a first control signal, and a second high voltage switch for transferring the high voltage generated outside the chip to the inside of the chip according to the clock signal and a second control signal. Therefore, it is possible to easily analyze fail of an initial product without manufacturing additional PMOS transistor that withstands a high voltage.